

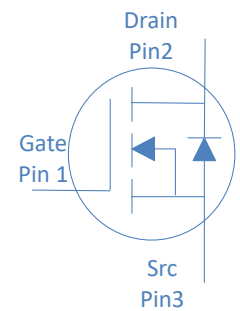
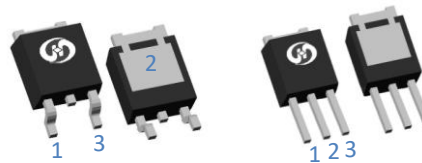
**65V N-Ch Power MOSFET**
**Feature**

- ◇ High Speed Power Switching, Logic level
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

$V_{DS}$		65	V
$R_{DS(on),typ}$	$V_{GS}=10V$	7.5	mΩ
$R_{DS(on),typ}$	$V_{GS}=4.5V$	10.5	mΩ
$I_D$ (Silicon Limited)		58	A

**Application**

- ◇ Synchronous Rectification in SMPS
- ◇ Hard Switching and High Speed Circuit
- ◇ DC/DC in Telecoms and Industrial

**TO-252**
**TO-251**


Part Number	Package	Marking
HGD090NE6AL	TO-252	GD090NE6AL
HGI090NE6AL	TO-251	GI090NE6AL

**Absolute Maximum Ratings at  $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^\circ\text{C}$	58	A
		$T_C=100^\circ\text{C}$	41	
Drain to Source Voltage	$V_{DS}$	-	65	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	270	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.4\text{mH}, T_C=25^\circ\text{C}$	45	mJ
Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	63	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	$^\circ\text{C}$

**Absolute Maximum Ratings**

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance Junction-Case	$R_{\theta JC}$	2.4	$^\circ\text{C/W}$

**Electrical Characteristics at  $T_j=25^{\circ}\text{C}$  (unless otherwise specified)**
**Static Characteristics**

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	65	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.4	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=60V, T_j=25^{\circ}\text{C}$	-	-	1	$\mu A$
		$V_{GS}=0V, V_{DS}=60V, T_j=100^{\circ}\text{C}$	-	-	100	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A$	-	7.5	9	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=5A$	-	10.5	13	$m\Omega$
Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=10A$	-	29	-	S
Gate Resistance	$R_G$	$V_{GS}=0V, V_{DS}$ Open, $f=1\text{MHz}$	-	1.4	-	$\Omega$

**Dynamic Characteristics**

Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=30V, f=1\text{MHz}$	-	1170	-	pF
Output Capacitance	$C_{oss}$		-	518	-	
Reverse Transfer Capacitance	$C_{rss}$		-	31	-	
Total Gate Charge	$Q_g(10V)$	$V_{DD}=30V, I_D=10A, V_{GS}=10V$	-	20.5	-	nC
Total Gate Charge	$Q_g(4.5V)$		-	10.5	-	
Gate to Source Charge	$Q_{gs}$		-	2.5	-	
Gate to Drain (Miller) Charge	$Q_{gd}$		-	5.5	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=10A, V_{GS}=10V,$ $R_G=10\Omega,$	-	7	-	ns
Rise time	$t_r$		-	4	-	
Turn off Delay Time	$t_{d(off)}$		-	22	-	
Fall Time	$t_f$		-	5	-	

**Reverse Diode Characteristics**

Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R=30V, I_F=10A, di_F/dt=100A/\mu s$	-	33	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	24	-	nC

Fig 1. Typical Output Characteristics

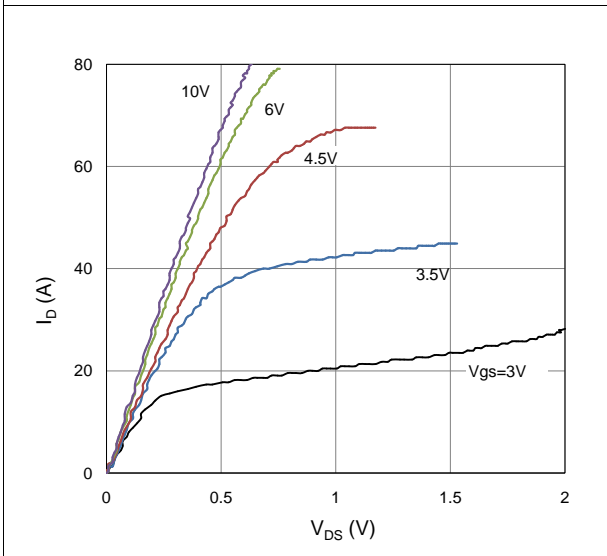


Figure 2. On-Resistance vs. Gate-Source Voltage

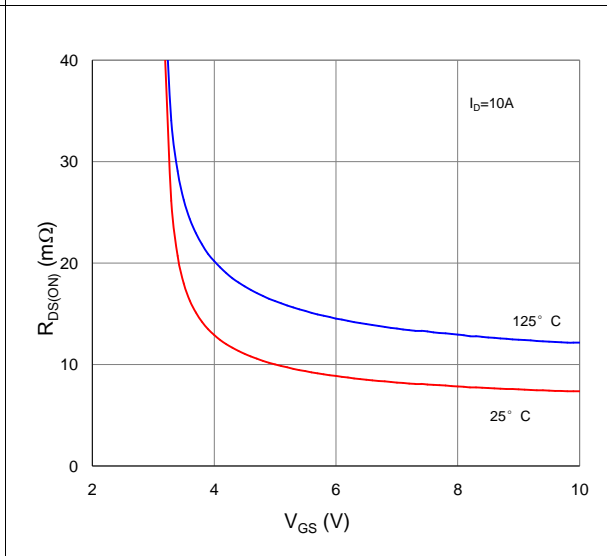


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

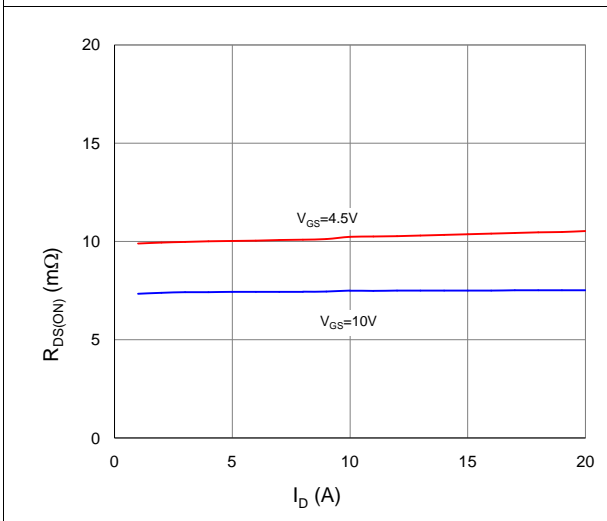


Figure 4. Normalized On-Resistance vs. Junction Temperature

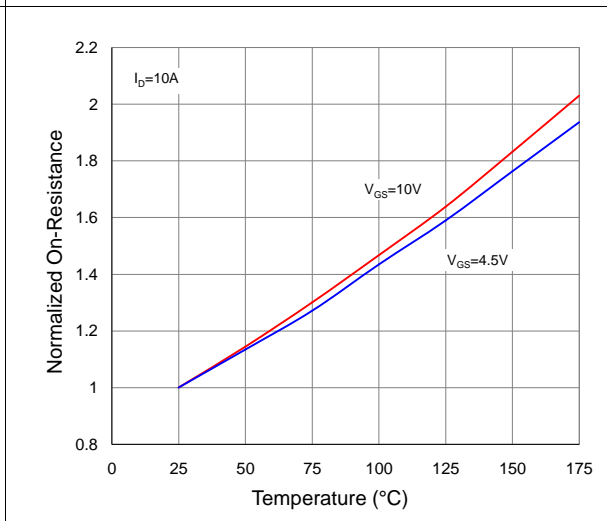


Figure 5. Typical Transfer Characteristics

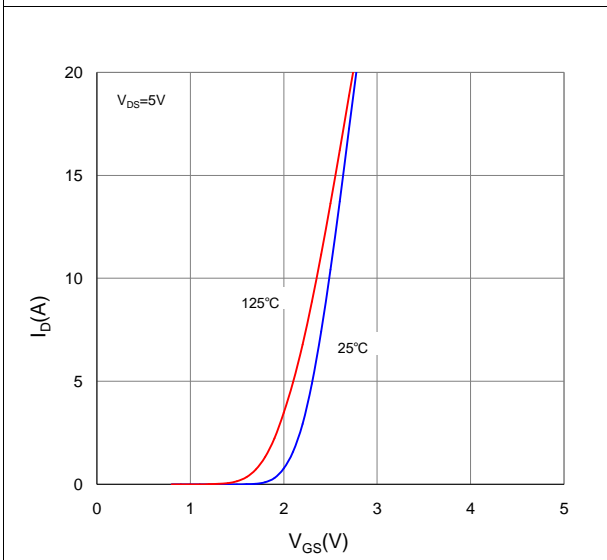


Figure 6. Typical Source-Drain Diode Forward Voltage

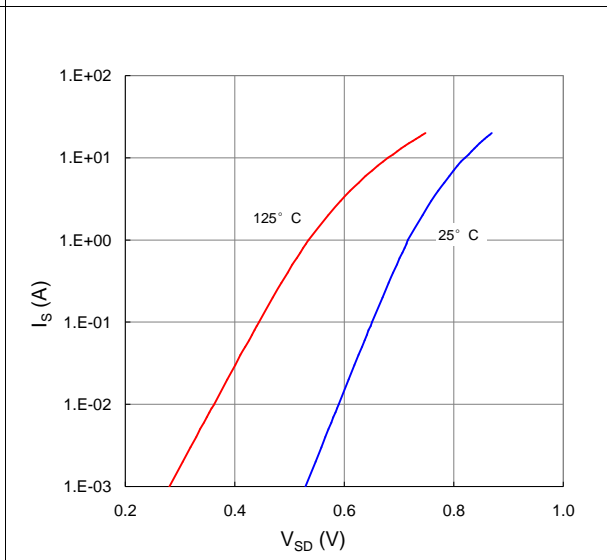


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

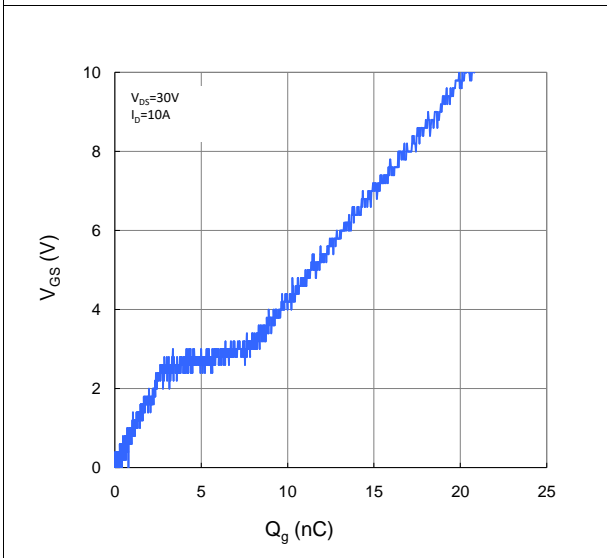


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

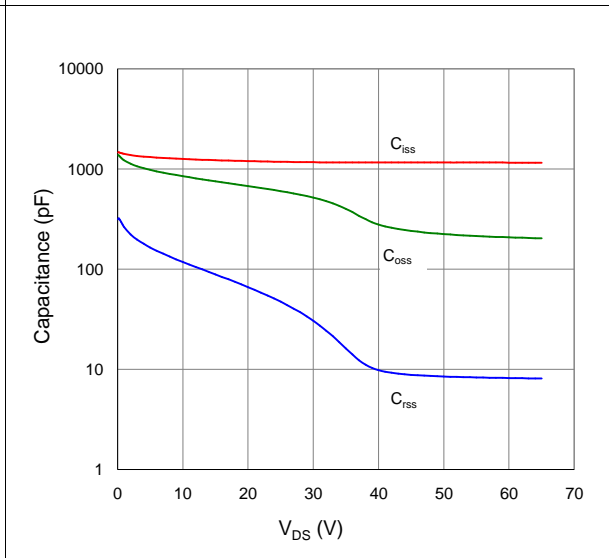


Figure 9. Maximum Safe Operating Area

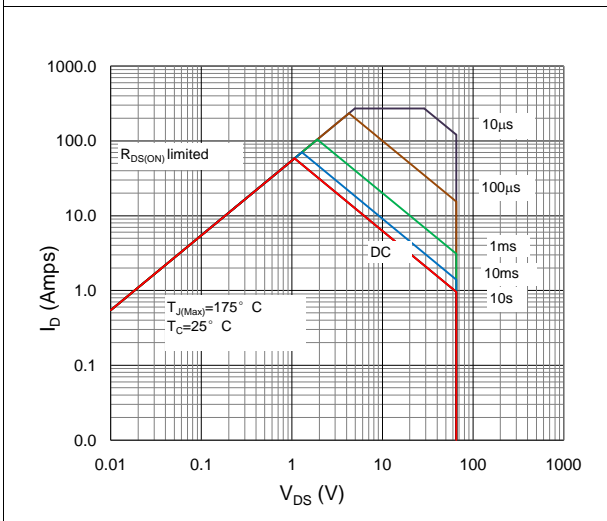


Figure 10. Maximum Drain Current vs. Case Temperature

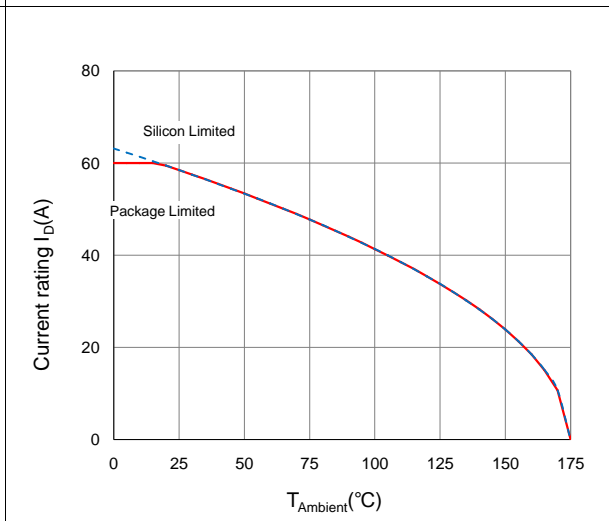
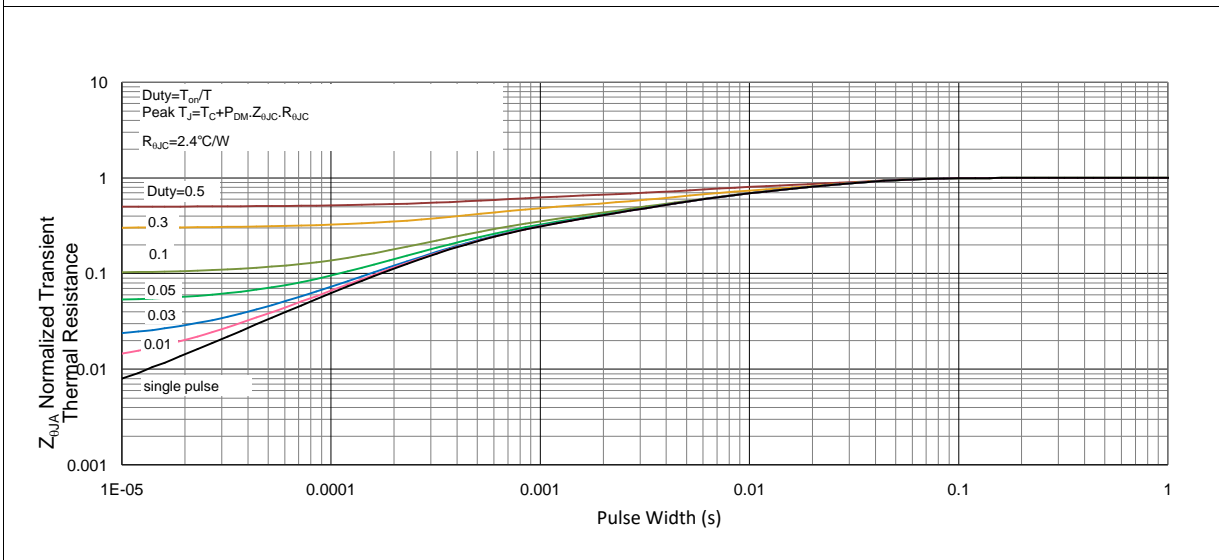
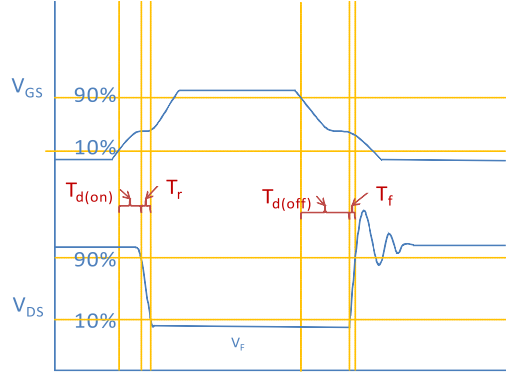
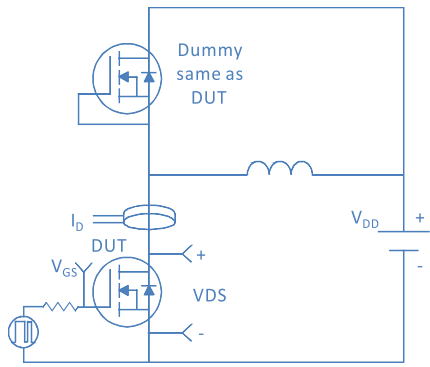


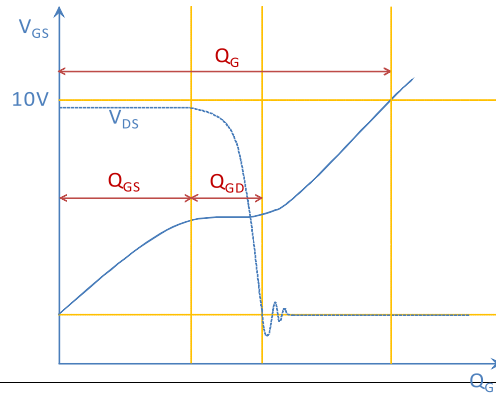
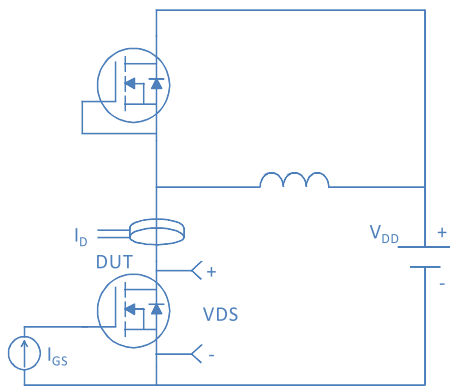
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



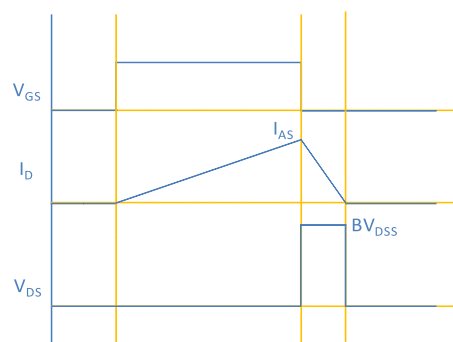
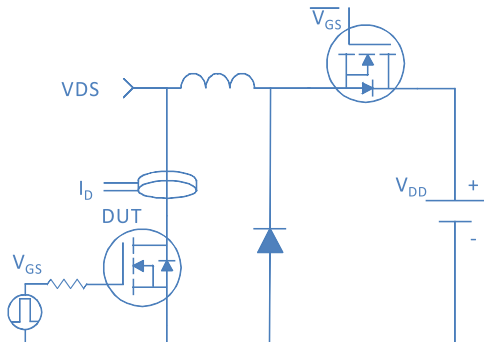
Inductive switching Test



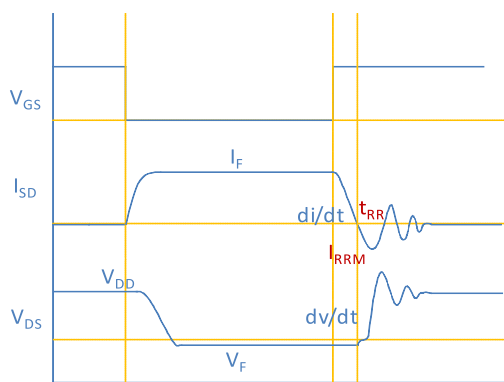
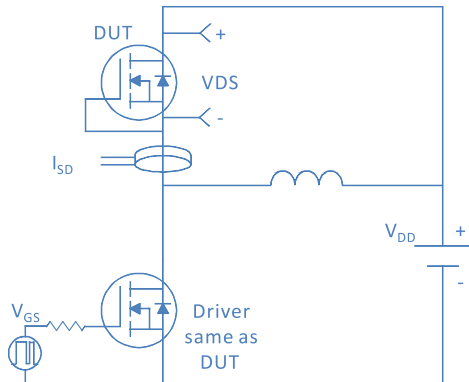
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

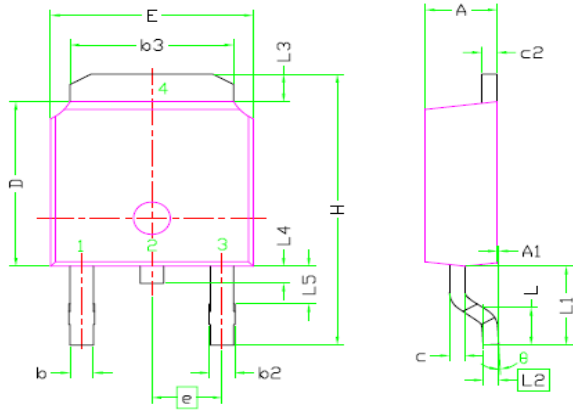


Diode Recovery Test

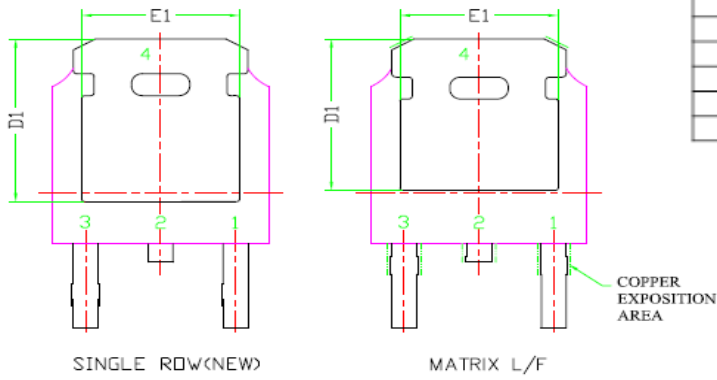


Package Outline

TO-252, 2 leads

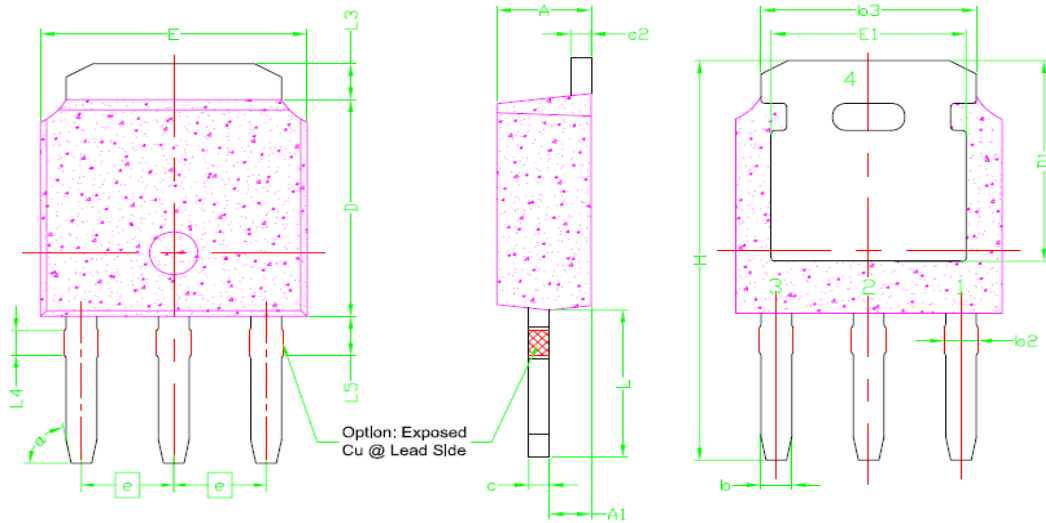


SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.46	0.50	0.60
c2	0.46	0.50	0.58
D1	5.21	--	--
E1	4.40	--	--
θ	0°	--	10°



Package Outline

TO-251, 3leads



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	3.98	4.13	4.28
L3	0.89	--	1.27
L4	0.698 REF		
L5	0.972	1.099	1.226
D	6.00	6.10	6.223
H	11.05	11.25	11.45
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0.89	1.04	1.15
c	0.46	0.50	0.60
c2	0.46	0.50	0.60
D1	5.10	--	--
E1	4.40	--	--
a	79° REF		